

N-Channel Enhancement MOSFET

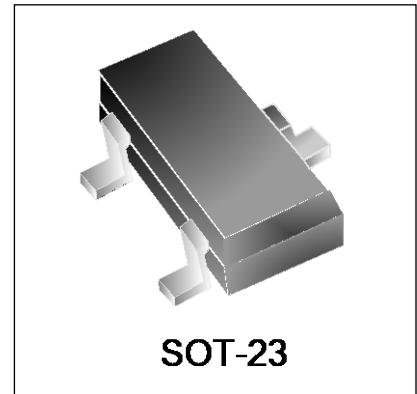
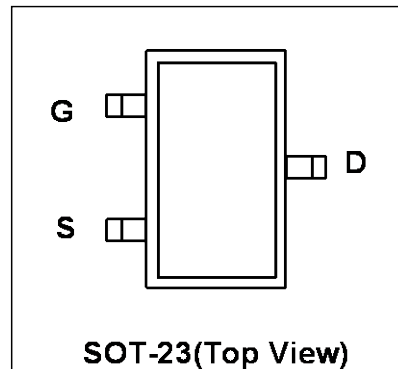
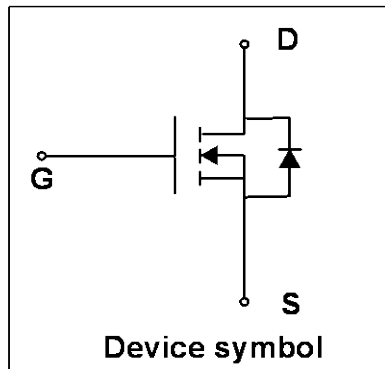
Features

- Way-on Small Signal MOSFETs
- $V_{DS} = 100V$, $I_D = 2A$
 $R_{DS(on)} < 280m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(on)} < 310m\Omega$ @ $V_{GS} = 4.5V$
- Trench LV MOSFET Technology

Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Absolute Maximum Rating ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	2	A
Pulsed Drain Current ¹	I_{DM}	8	A
Power Dissipation	P_D	1.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	105	$^\circ C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V_{(BR)DSS}	V _{GS} = 0 V, I _D = 250μA	100	-	-	V
Gate Leakage Current	I_{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Drain Cut-off Current	I_{DSS}	V _{DS} = 100V, V _{GS} = 0V	-	-	1	μA
Gate Threshold Voltage	V_{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	1.1	1.5	2.5	V
Drain-Source on-state Resistance ³	R_{DS(on)}	V _{GS} = 10V, I _D = 2A	-	220	280	mΩ
		V _{GS} = 4.5V, I _D = 1.5A	-	240	310	
Dynamic Characteristics ⁴						
Input Capacitance	C_{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz	-	440	-	pF
Output Capacitance	C_{oss}		-	14	-	
Reverse Transfer Capacitance	C_{rss}		-	10	-	
Switching Characteristics ⁴						
Total gate charge	Q_g	V _{GS} = 10V, V _{DS} = 50V, I _D = 2A	-	5.3	-	nC
Gate-source charge	Q_{gs}		-	1.4	-	
Gate-drain charge	Q_{gd}		-	1.8	-	
Turn-on Time	t_{d(on)}	V _{GS} = 10V, V _{DD} = 50V, R _G = 1Ω, I _D = 2A	-	14	-	ns
Rise time	t_f		-	54	-	
Turn-off Time	t_{d(off)}		-	18	-	
Fall time	t_f		-	11	-	
Source-Drain Diode characteristics						
Body Diode Voltage ³	V_{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	I_S		-	-	2	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
2. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

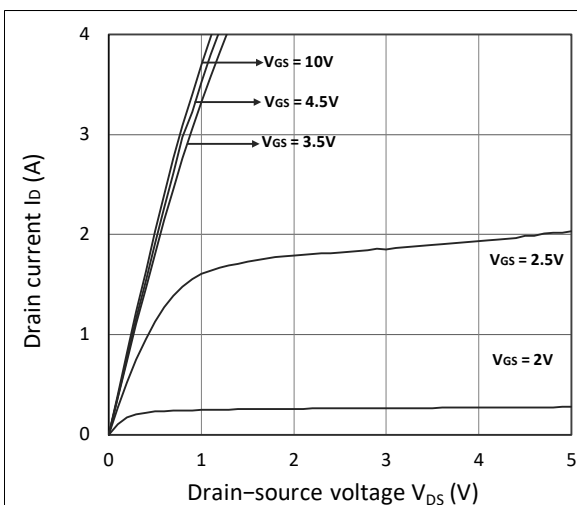


Figure 1. Output Characteristics

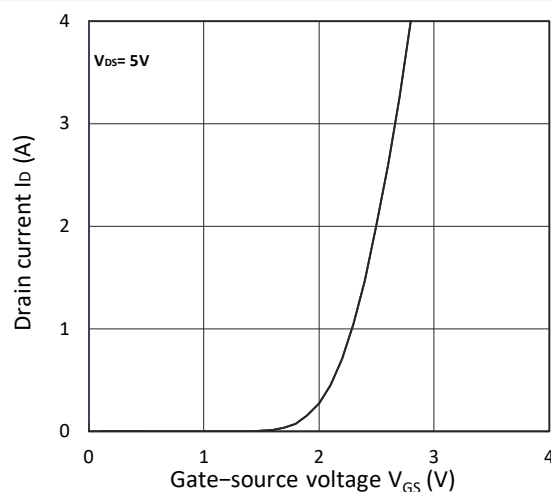


Figure 2. Transfer Characteristics

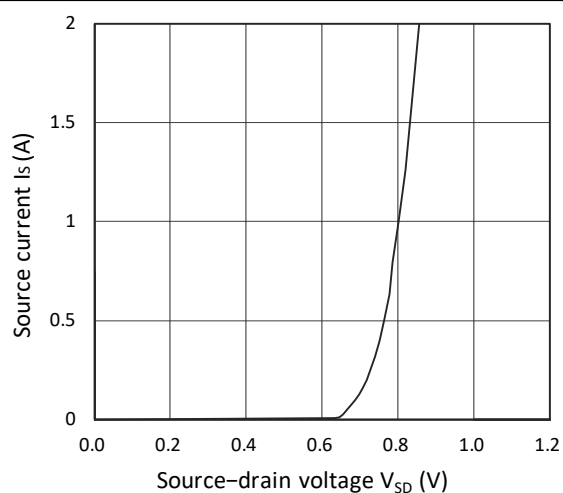
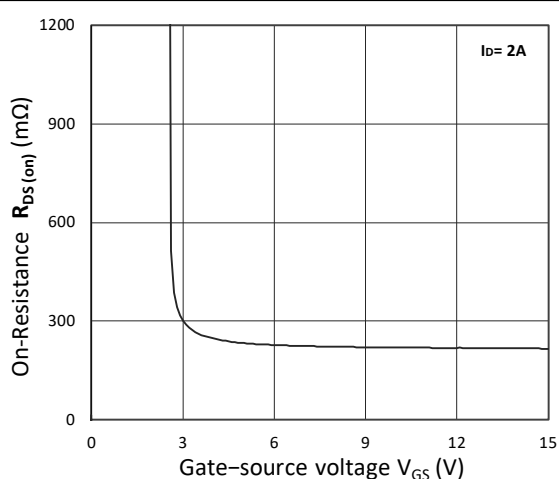
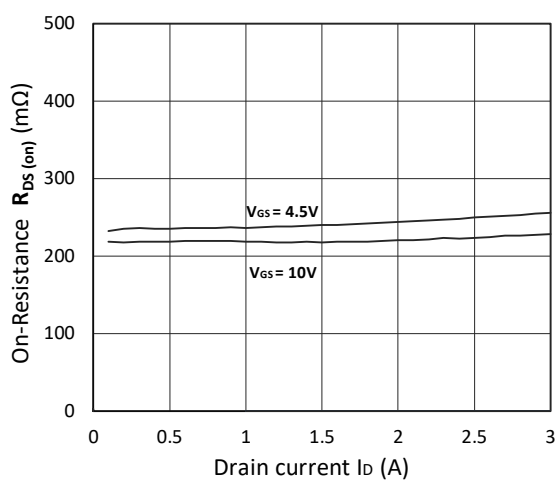
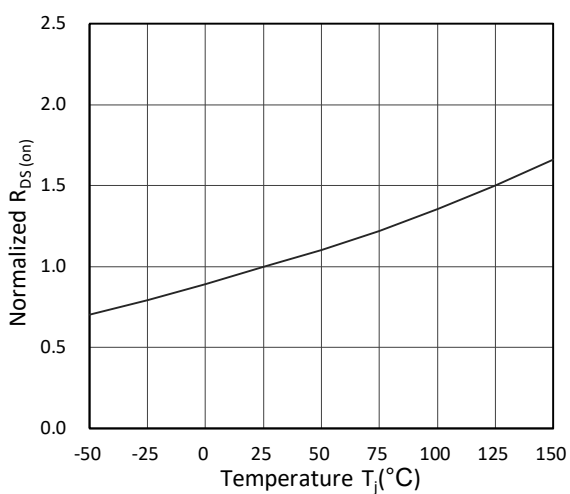


Figure 3. Forward Characteristics of Reverse

Figure 4. $R_{DS(on)}$ vs. V_{GS} Figure 5. $R_{DS(on)}$ vs. I_D Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

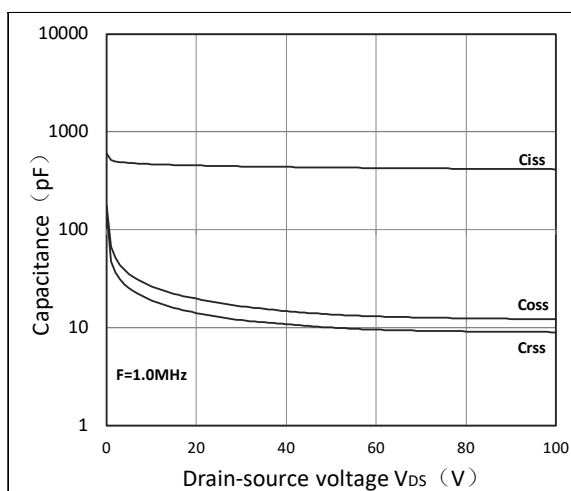


Figure 7. Capacitance Characteristics

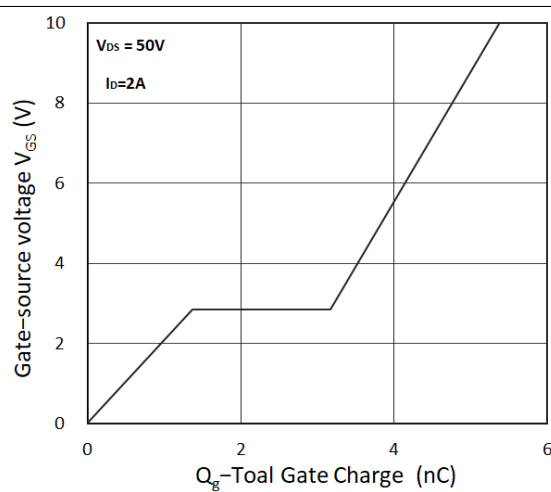
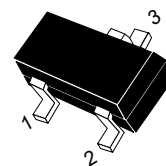
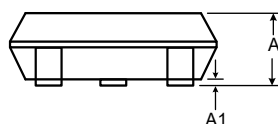
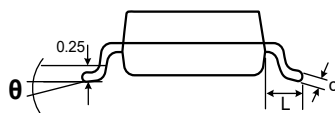
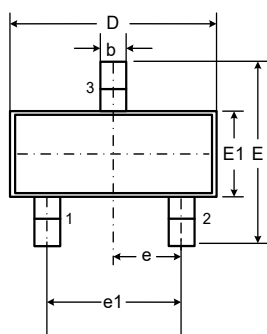


Figure 8. Gate Charge Characteristics

Outline Drawing – SOT-23

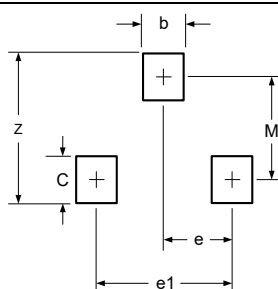
PACKAGE OUTLINE



SOT-23

DIMENSIONS

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037BSC	
e1	1.80	2.00	0.071	0.079
L	0.55REF		0.022REF	
θ	0°	8°	0°	8°

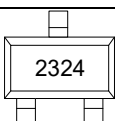


DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.080	2.02
C	0.032	0.80
Z	0.111	2.82
e	0.037 BSC	0.95 BSC
e1	0.075 BSC	1.90 BSC
b	0.032	0.80

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM10N20M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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For additional information, please contact your local Sales Representative.



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Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time. Users should verify actual device performance in their specific applications.